

High Frequency Switched Capacitor Voltage Converters with Shutdown in SOT Packages

Features

- Charge Pumps in 6-Pin SOT-23A Package
- 96% Voltage Conversion Efficiency
- Voltage Inversion and/or Doubling
- Operates from +1.8V to +5.5V
- Up to 25mA Output Current
- Only Two External Capacitors Required
- Power-Saving Shutdown Mode
- Fully Compatible with 1.8V Logic Systems

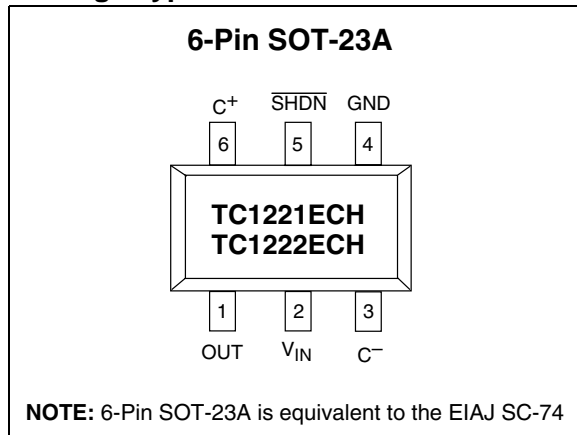
Applications

- LCD Panel Bias
- Cellular Phones
- Pagers
- PDAs, Portable Data Loggers
- Battery-Powered Devices

Device Selection Table

Part Number	Package	Osc. Freq. (kHz)	Operating Temp. Range
TC1221ECH	6-Pin SOT-23A	125	-40°C to +85°C
TC1222ECH	6-Pin SOT-23A	750	-40°C to +85°C

Package Type



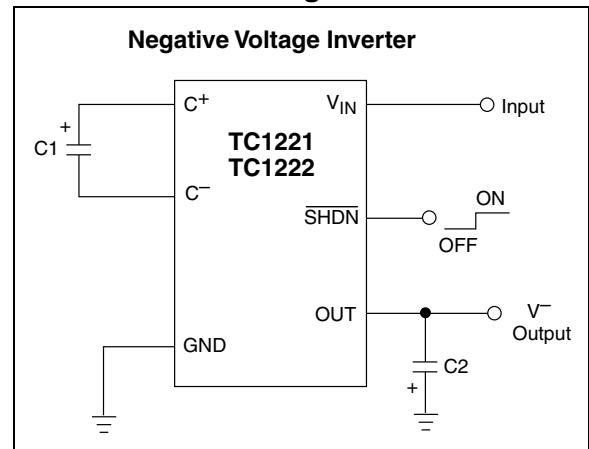
General Description

The TC1221/TC1222 are CMOS “charge-pump” voltage converters in ultra-small 6-Pin SOT-23A packages. They invert and/or double an input voltage which can range from +1.8V to +5.5V. Conversion efficiency is typically 96%. Switching frequency is 125kHz for the TC1221, 750kHz for the TC1222. When the shutdown pin is held at a logic low, the device goes into a very low power mode of operation, consuming less than 1µA of supply current.

For standard voltage inverter applications, the device requires only two external capacitors. With a few additional components a positive doubler can also be built. All other circuitry, including control, oscillator, power MOSFETs are integrated on-chip. Typical supply currents are 290µA (TC1221) and 1800µA (TC1222).

All devices are available in 6-pin SOT-23A surface mount packages.

Functional Block Diagram



TC1221/TC1222

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

Input Voltage (V_{IN} to GND).....	+6.0V, -0.3V
Output Voltage (OUT to GND).....	-6.0V, +0.3V
Current at OUT Pin.....	50mA
Short-Circuit Duration – OUT to GND	Indefinite
Power Dissipation ($T_A \leq 70^\circ\text{C}$)	
6-Pin SOT-23A	240mW
Operating Temperature Range.....	-40°C to +85°C
Storage Temperature (Unbiased)	-65°C to +150°C

*Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

TC1121 ELECTRICAL SPECIFICATIONS

Electrical Characteristics: $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{IN} = +5\text{V}$, $C_1 = C_2 = 1\mu\text{F}$, (TC1221), $C_1 = C_2 = 0.22\mu\text{F}$ (TC1222), Typical values are at $T_A = +25^\circ\text{C}$.

Symbol	Parameter	Min	Typ	Max	Units	Device	Test Conditions
I_{DD}	Supply Current	—	290	600	μA	TC1221 TC1222	
		—	1800	2800			
I_{SHDN}	Shutdown Supply Current	—	0.01	1.0	μA		$\overline{\text{SHDN}} = \text{GND}$, $V_{IN} = 5\text{V}$ (Note 2)
V_{MIN}	Minimum Supply Voltage	1.8	—	—	V		$R_{LOAD} = 1\text{k}\Omega$
V_{MAX}	Maximum Supply Voltage	—	—	5.5	V		$R_{LOAD} = 1\text{k}\Omega$
F_{OSC}	Oscillator Frequency	81	125	169	kHz	TC1221 TC1222	
		550	750	950			
V_{IH}	$\overline{\text{SHDN}}$ Input Logic High	1.4	—	—	V		$V_{IN} = V_{MIN}$ to V_{MAX}
V_{IL}	$\overline{\text{SHDN}}$ Input Logic Low	—	—	0.4	V		$V_{IN} = V_{MIN}$ to V_{MAX}
P_{EFF}	Power Efficiency	—	90	—	%	TC1221 TC1222	$R_{LOAD} = 1\text{k}\Omega$
		—	70	—			
V_{EFF}	Voltage Conversion Efficiency	94	96	—	%		$R_{LOAD} = \infty$
R_{OUT}	Output Resistance	—	25	65	Ω		$I_{LOAD} = 0.5\text{mA}$ to 25mA (Note 1)
		—	—	—			
T_{WK}	Wake-up Time From Shutdown Mode	—	80	—	μsec	TC1221 TC1222	$R_{LOAD} = 1\text{k}\Omega$
		—	25	—			

- Note** 1: Capacitor contribution is approximately 20% of the output impedance [ESR = $1/\text{pump frequency} \times \text{capacitance}$].
 2: V_{IN} is guaranteed to be disconnected from OUT when the converter is in shutdown..

2.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 2-1.

TABLE 2-1: PIN FUNCTION TABLE

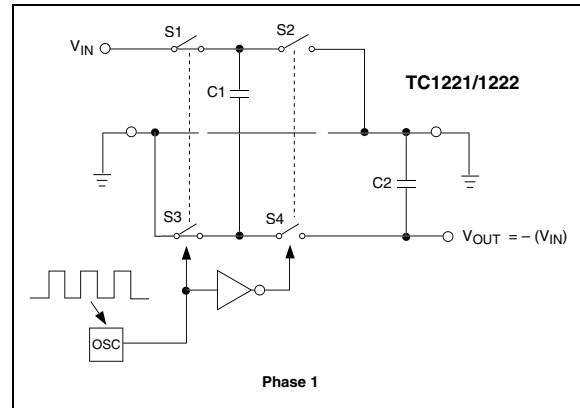
Pin No. (6-Pin SOT-23A)	Symbol	Description
1	OUT	Inverting charge pump output.
2	V_{IN}	Positive power supply input.
3	C^-	Commutation capacitor negative terminal.
4	GND	Ground.
5	$\overline{\text{SHDN}}$	Shutdown input (active low).
6	C^+	Commutation capacitor positive terminal.

TC1221/TC1222

3.0 DETAILED DESCRIPTION

The TC1221/TC1222 charge pump converters invert the voltage applied to the V_{IN} pin. Conversion consists of a two-phase operation (Figure 3-1). During the first phase, switches S2 and S4 are opened and S1 and S3 are closed. During this time, C1 charges to the voltage on V_{IN} and load current is supplied from C2. During the second phase, S2 and S4 are closed, and S1 and S3 are opened. This action connects C1 across C2, restoring charge to C2.

FIGURE 3-1: IDEAL SWITCHED CAPACITOR CHARGE PUMP



4.0 APPLICATIONS INFORMATION

4.1 Output Voltage Considerations

The TC1221/TC1222 perform voltage conversion but do not provide *regulation*. The output voltage will droop in a linear manner with respect to load current. The value of this equivalent output resistance is approximately 25Ω nominal at +25°C and $V_{IN} = +5V$. V_{OUT} is approximately -5V at light loads, and droops according to the equation below:

$$V_{DROP} = I_{OUT} \times R_{OUT}$$

$$V_{OUT} = -(V_{IN} - V_{DROP})$$

4.2 Charge Pump Efficiency

The overall power efficiency of the charge pump is affected by four factors:

1. Losses from power consumed by the internal oscillator, switch drive, etc. (which vary with input voltage, temperature and oscillator frequency).
2. I^2R losses due to the on-resistance of the MOSFET switches on-board the charge pump.
3. Charge pump capacitor losses due to effective series resistance (ESR).
4. Losses that occur during charge transfer (from the commutation capacitor to the output capacitor) when a voltage difference between the two capacitors exists.

Most of the conversion losses are due to factors (2) and (3) above. These losses are given by Equation 4-1(b).

EQUATION 4-1:

$$a) P_{LOSS(2,3)} = I_{OUT}^2 \times R_{OUT}$$

$$b) \text{ where } R_{OUT} = \left[1 / [f_{OSC}(C1)] + 8R_{SWITCH} + 4ESR_{C1} + ESR_{C2} \right]$$

The $1/(f_{OSC})(C1)$ term in Equation 4-1(b) is the effective output resistance of an ideal switched capacitor circuit (Figure 4-1 and Figure 4-2). The value of R_{SWITCH} can be approximated at 0.5Ω for the TC1221/TC1222.

The remaining losses in the circuit are due to factor (4) above, and are shown in Equation 4-2. The output voltage ripple is given by Equation 4-3.

EQUATION 4-2:

$$P_{LOSS(4)} = [(0.5)(C1)(V_{IN}^2 - V_{OUT}^2) + (0.5)(C2)(V_{RIPPLE}^2 - 2V_{OUT} V_{RIPPLE})] \times f_{OSC}$$

EQUATION 4-3:

$$V_{RIPPLE} = [I_{OUT} / 2 \times (f_{OSC})(C2)] + 2(I_{OUT})(ESR_{C2})$$

FIGURE 4-1: IDEAL SWITCHED CAPACITOR MODEL

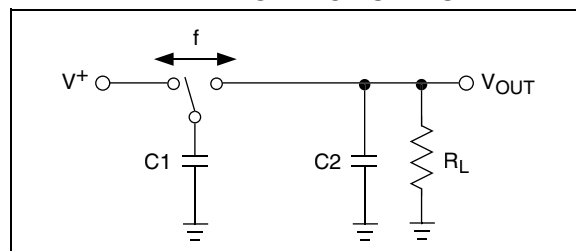
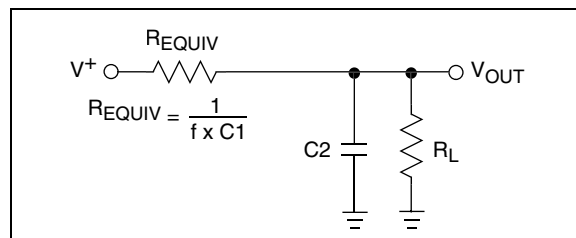


FIGURE 4-2: EQUIVALENT OUTPUT RESISTANCE



4.3 Capacitor Selection

In order to maintain the lowest output resistance and output ripple voltage, it is recommended that low ESR capacitors be used. Additionally, larger values of $C1$ will lower the output resistance and larger values of $C2$ will reduce output ripple. (Equation 4-1(b) and Equation 4-3).

4.7 Cascading Devices

Two or more TC1221/TC1222 can be cascaded to increase output voltage (Figure 4-4). If the output is lightly loaded, it will be close to $(-2 \times V_{IN})$ but will droop at least by R_{OUT} of the first device multiplied by the I_Q of the second. It can be seen that the output resistance rises rapidly for multiple cascaded devices.

4.8 Paralleling Devices

To reduce the value of R_{OUT} , multiple TC1221/TC1222's can be connected in parallel (Figure 4-5). The output resistance will be reduced by a factor of N where N is the number of TC1221/TC1222. Each device will require its own pump capacitor (C1), but all devices may share one reservoir capacitor (C2). However, to preserve ripple performance the value of C2 should be scaled according to the number of paralleled TC1221/TC1222.

FIGURE 4-4: CASCADING MULTIPLE DEVICES TO INCREASE OUTPUT VOLTAGE

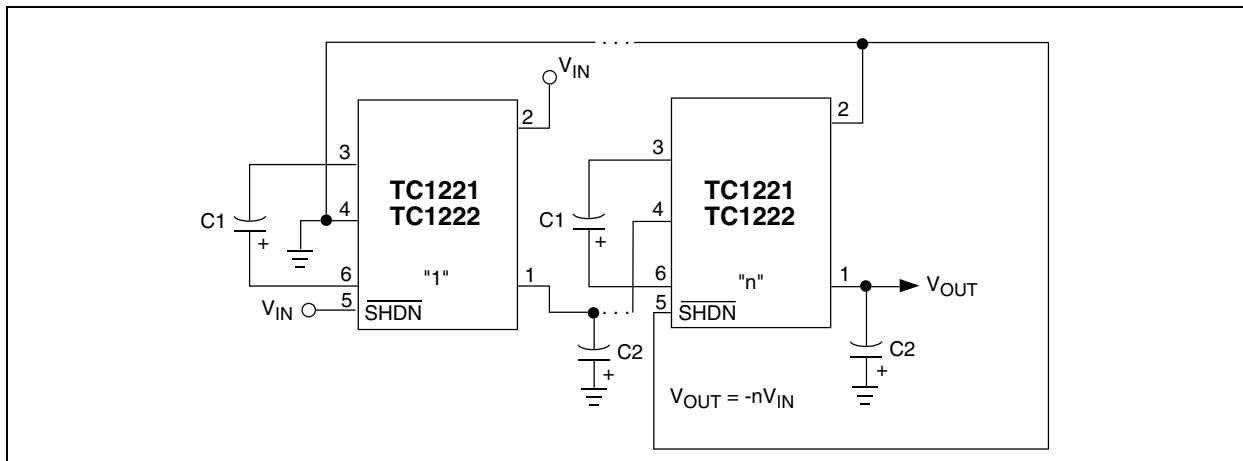
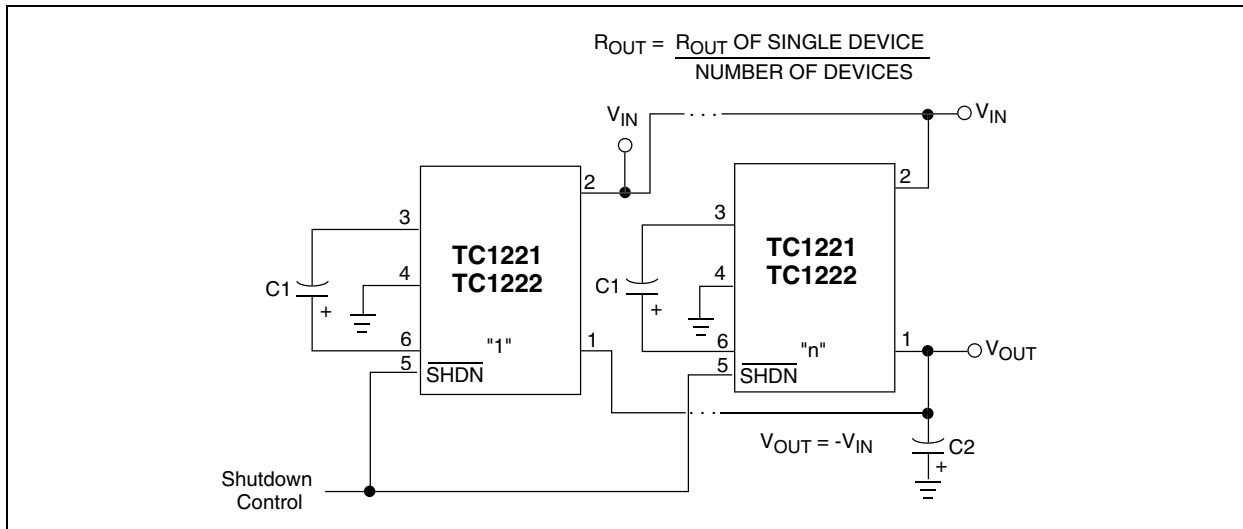


FIGURE 4-5: PARALLELING MULTIPLE DEVICES TO REDUCE OUTPUT RESISTANCE



TC1221/TC1222

4.9 Voltage Doubler/Inverter

Another common application of the TC1221/TC1222 is shown in Figure 4-6. This circuit performs two functions in combination. C1 and C2 form the standard inverter circuit described above. C3 and C4 plus the two diodes form the voltage doubler circuit. C1 and C3 are the pump capacitors and C2 and C4 are the reservoir capacitors. Because both sub-circuits rely on the same switches if either output is loaded, both will droop toward GND. Make sure that the total current drawn from both the outputs does not total more than 40mA.

4.10 Diode Protection for Heavy Loads

When heavy loads require the OUT pin to sink large currents being delivered by a positive source, diode protection may be needed. The OUT pin should not be allowed to be pulled above ground. This is accomplished by connecting a Schottky diode (1N5817) as shown in Figure 4-7.

4.11 Layout Considerations

As with any switching power supply circuit, good layout practice is recommended. Mount components as close together as possible to minimize stray inductance and capacitance. Noise leakage into other circuitry can be minimized with the use of a large ground plane.

FIGURE 4-6: COMBINED DOUBLER AND INVERTER

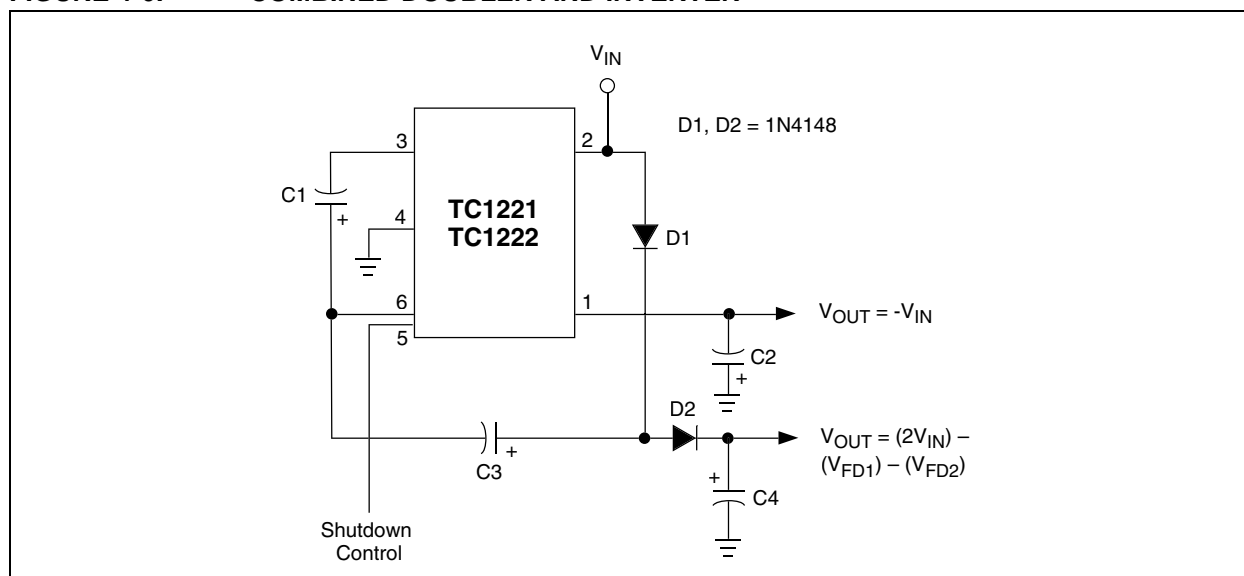
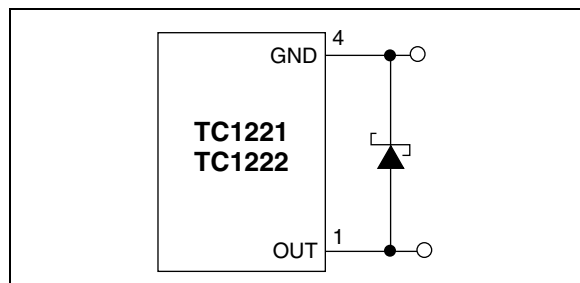


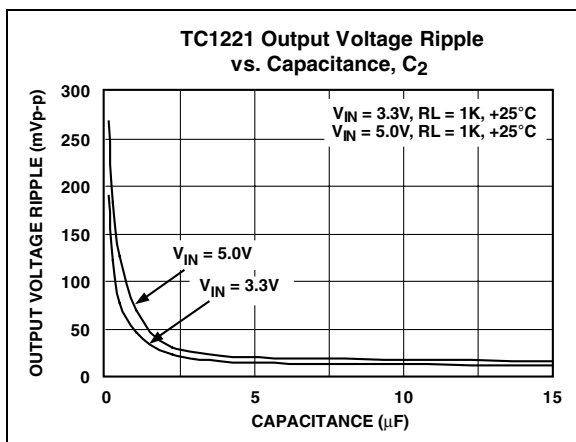
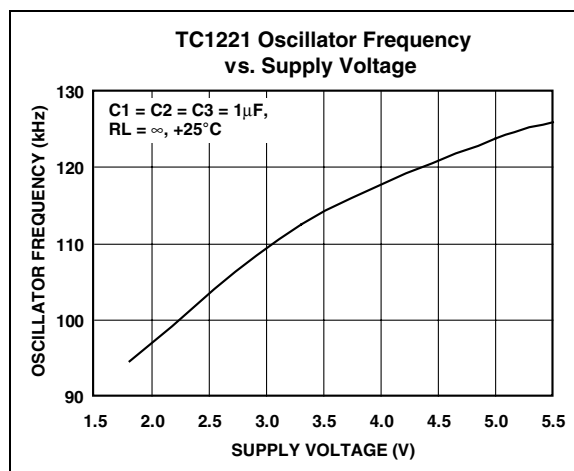
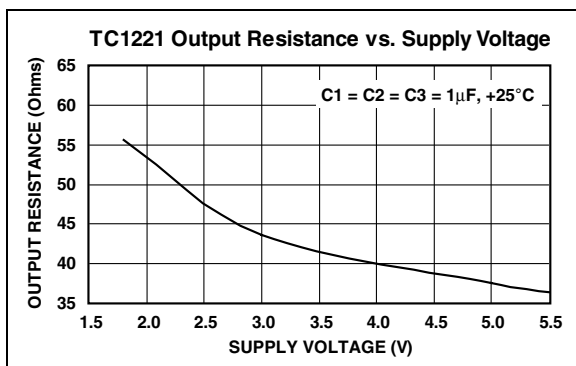
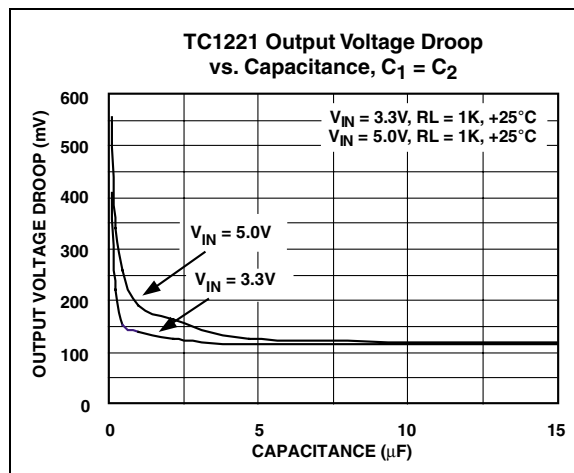
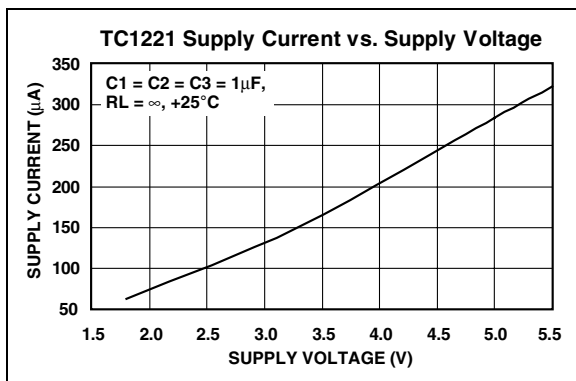
FIGURE 4-7: HIGH V- LOAD CURRENT



5.0 TYPICAL CHARACTERISTICS

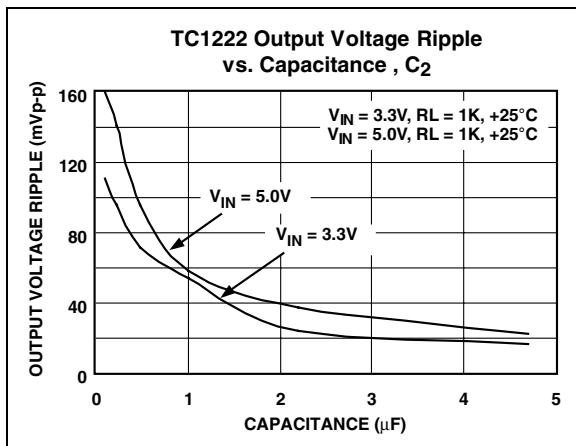
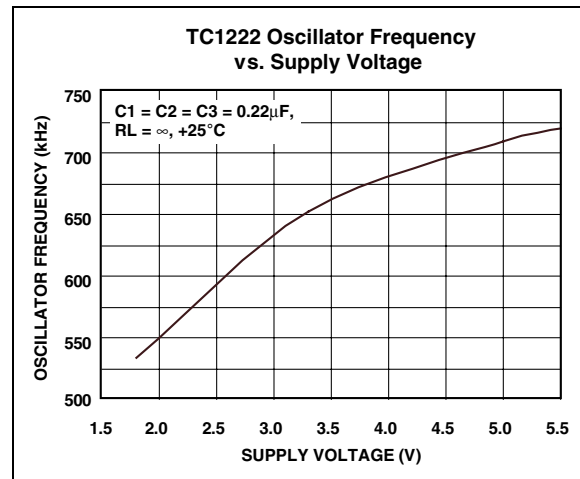
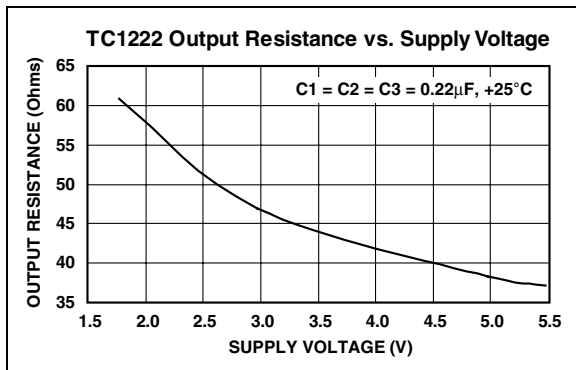
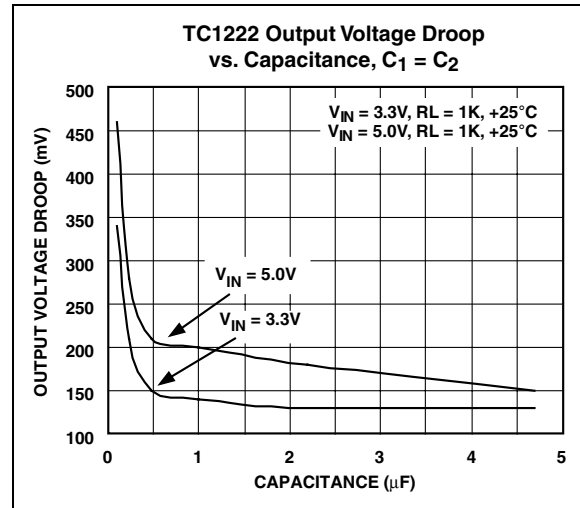
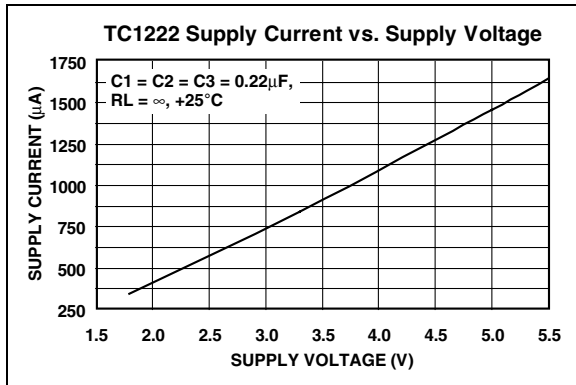
Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Circuit of Figure 4-3, $V_{IN} = +5V$, $C1 = C2 = C3$, $T_A = 25^\circ C$ unless otherwise noted.



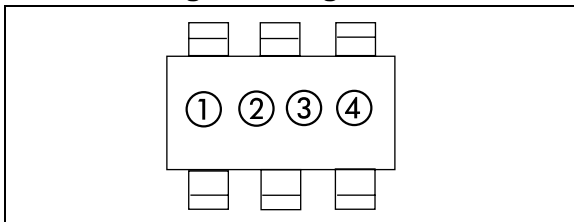
TC1221/TC1222

5.0 TYPICAL CHARACTERISTICS (CONTINUED)



6.0 PACKAGING INFORMATION

6.1 Package Marking Information



① & ② = part number code + temperature range
(two-digit code)

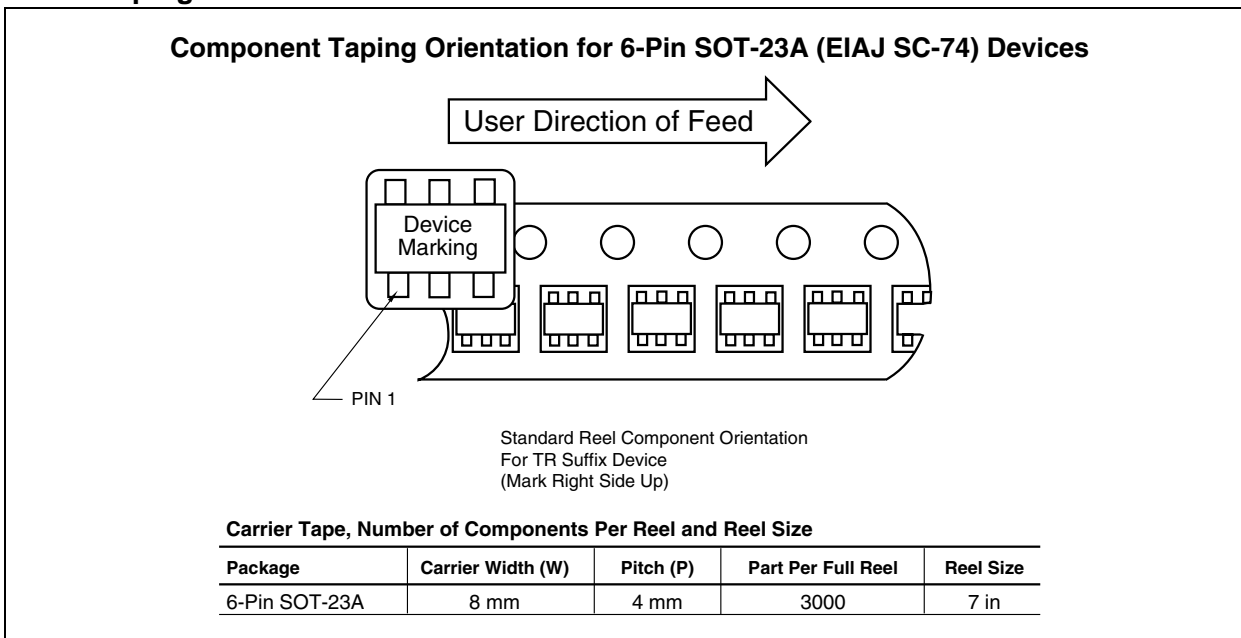
TC1221/TC1222	Code
TC1221ECH	GA
TC1222ECH	GB

ex: 1221ECH = ⓐ Ⓐ ○ ○
1222ECH = ⓐ Ⓑ ○ ○

③ represents year and 2-month code

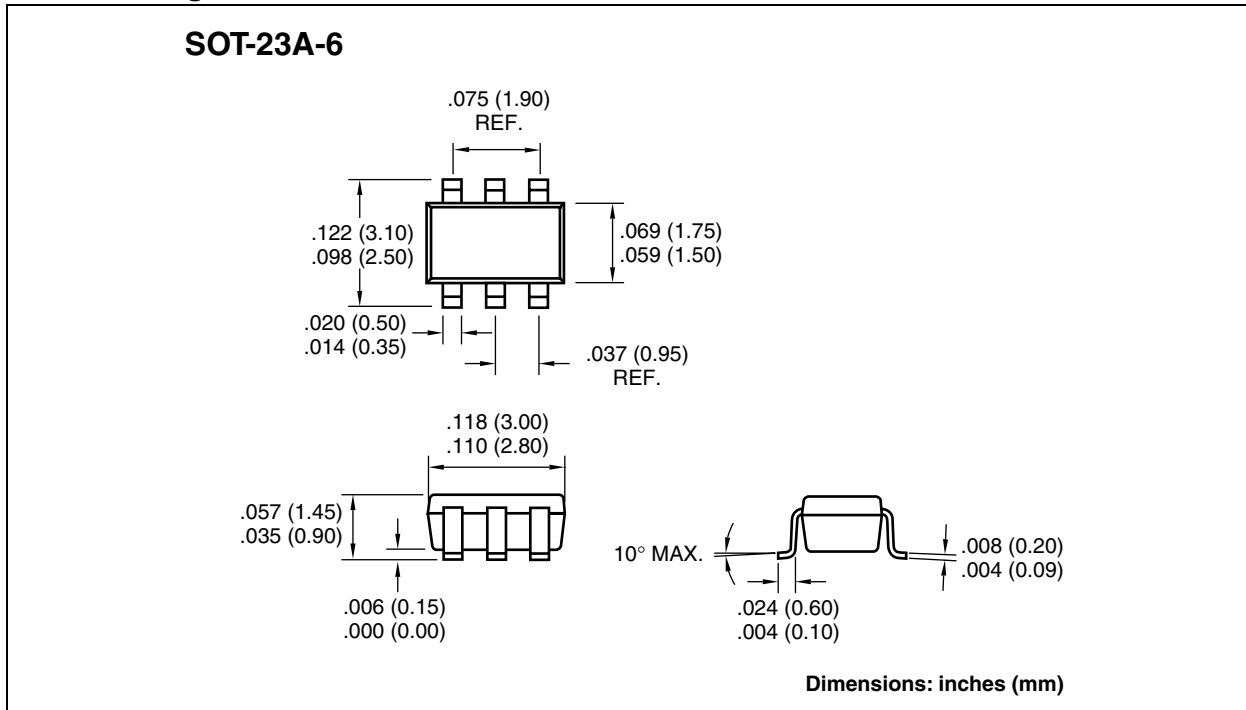
④ represents production lot ID code

6.2 Taping Form



TC1221/TC1222

6.3 Package Dimensions



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TC1221/TC1222

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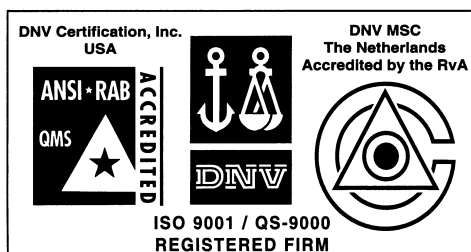
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